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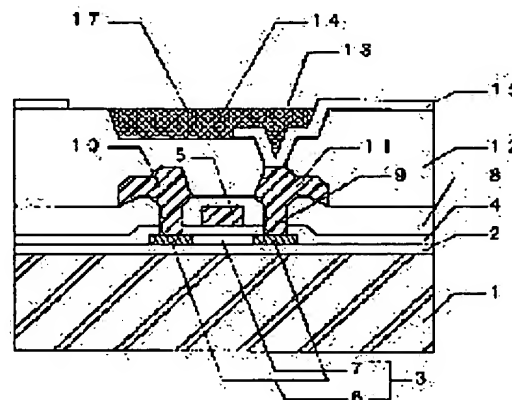
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(54) ACTIVE MATRIX TYPE LIQUID CRYSTAL DISPLAY DEVICE AND ITS PRODUCTION

(57)Abstract:

PROBLEM TO BE SOLVED: To provide an active matrix type liquid crystal display device which is bright and has a high contrast and a process for producing the same.

SOLUTION: Base coating layer 2, active layer 3, a gate insulating film 4 and a gate electrode 5 are formed to a prescribed shape on an insulative substrate 1. Source regions, drain regions 6 and channel regions 7 are formed on the active layer 3. An interlayer insulating film 8 is thereafter formed over the entire surface and is opened with contact holes 9 where source electrodes 10 and drain electrodes 11 are formed. A planarization film 12 is then formed over the entire surface and is opened with contact holes 13. In succession, the regions on the TFTs of the planarization film 12 are dug down by etching to form recessed parts 14. Pixel electrodes 15 are electrically connected to the drain electrodes 11. Next, a black resin is applied over the entire surface and the contact holes 13 and the recessed parts 14 are filled with the black resin. The entire surface is etched back to expose the surface of the pixel electrodes 15 and light shielding films 17 are formed on the TFTs(thin-film transistors).



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